



General Description

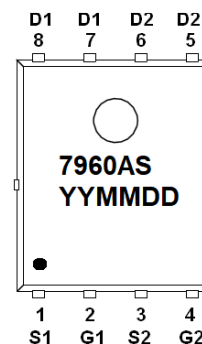
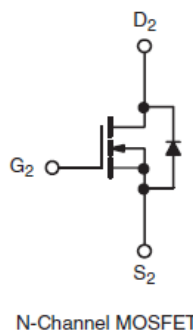
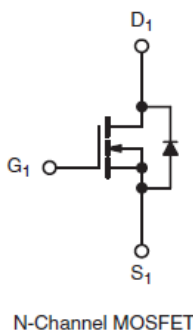
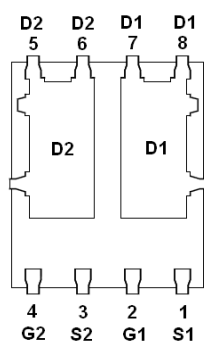
AFN7960AS, Dual N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- $I_D=12A, R_{DS(ON)}= 20m\Omega@V_{GS}=10V$
- $I_D=10A, R_{DS(ON)}= 24m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- DFN 5X6-8L package design

Pin Description (DFN5X6-8L)



Application

- Motor and Load Control
- Power Management in White LED System
- LCD TV Inverter & AD/DC Inverter Systems.

Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN7960ASFN568RG	7960AS	DFN 5X6-8L	Tape & Reel	2500 EA

- ※ 7960AS : Parts Code
- ※ YYMMDD : Date Code
- ※ AFN7960ASFN568RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings (T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	12
		T _A =85°C	10
Pulsed Drain Current	I _{DM}	40	A
Continuous Source Current(Diode Conduction)	I _S	2.9	A
Power Dissipation	P _D	T _A =25°C	3.5
		T _A =70°C	2.2
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

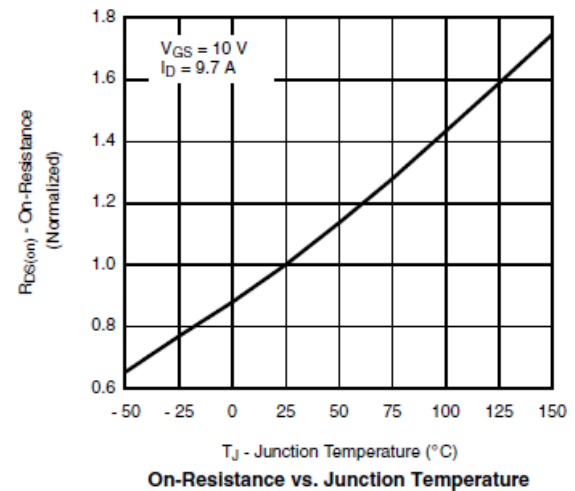
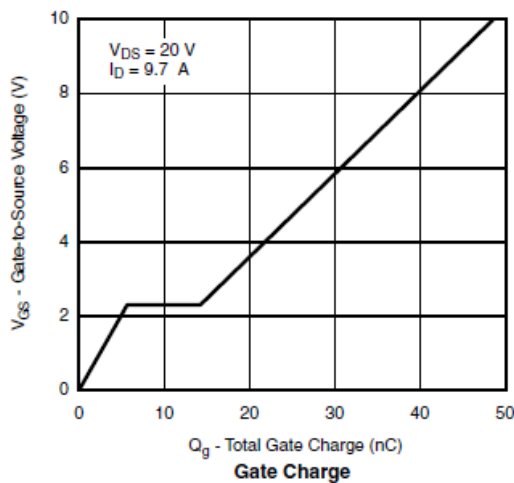
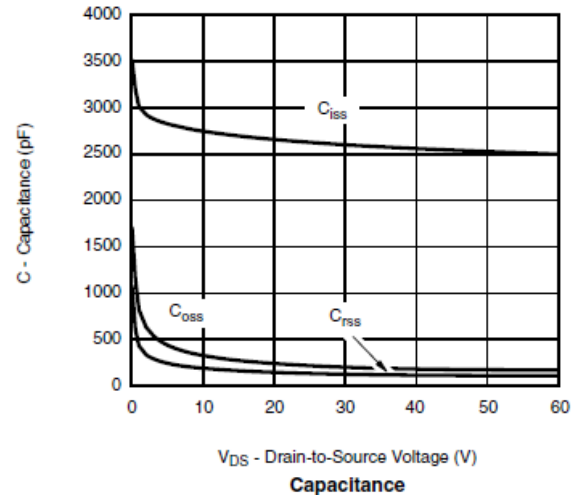
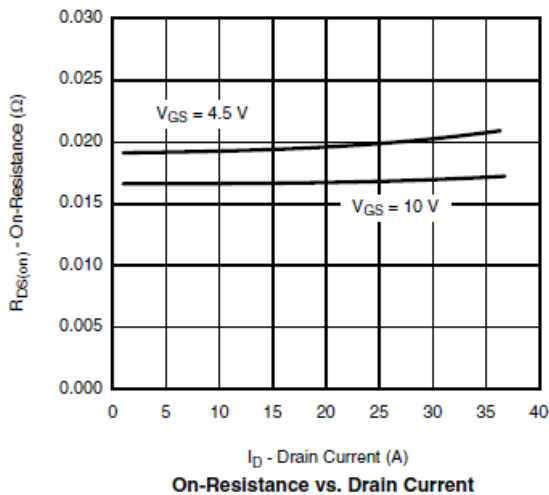
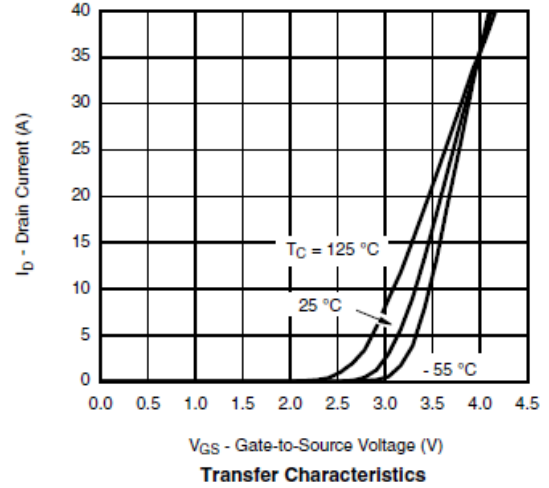
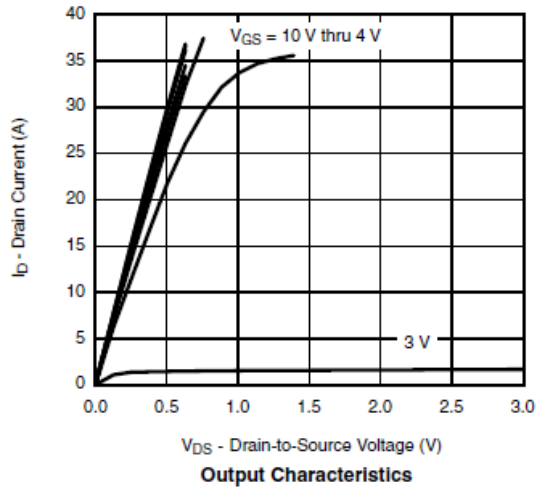
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0		2.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	uA
		V _{DS} =48V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =10V	30			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A		17	20	mΩ
		V _{GS} =4.5V, I _D =10A		19	24	
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =5.3A		24		S
Diode Forward Voltage	V _{SD}	I _S =2.0A, V _{GS} =0V		0.85	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =10V I _D ≅9.7A		50	75	nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			9		
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V f=1MHz		3200		pF
Output Capacitance	C _{oss}			300		
Reverse Transfer Capacitance	C _{rss}			250		
Turn-On Time	t _{d(on)}	V _{DD} =30V, R _L =30Ω I _D ≅1A, V _{GEN} =10V R _G =6Ω		12	20	ns
	t _r			12	20	
Turn-Off Time	t _{d(off)}			60	90	
	t _f			20	30	

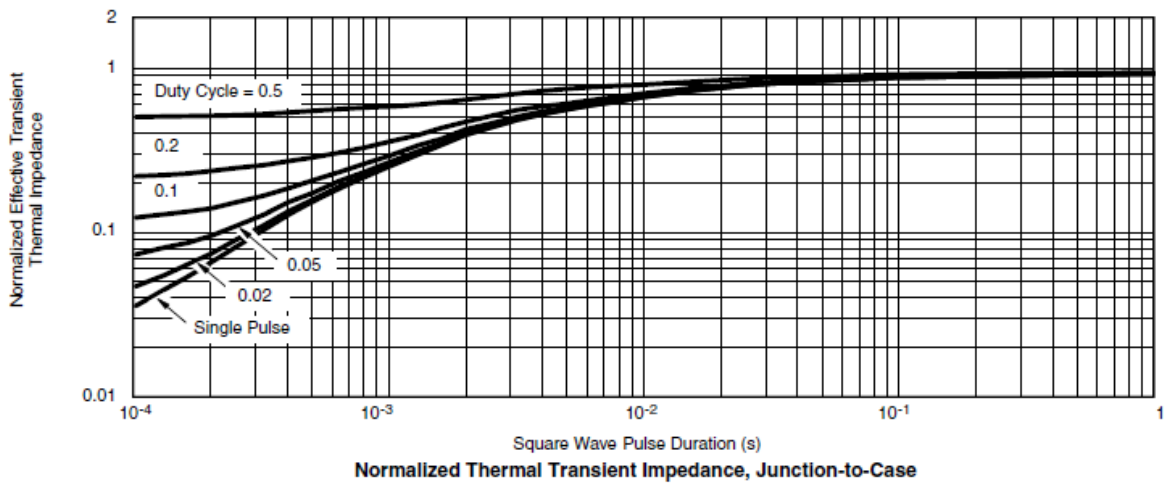
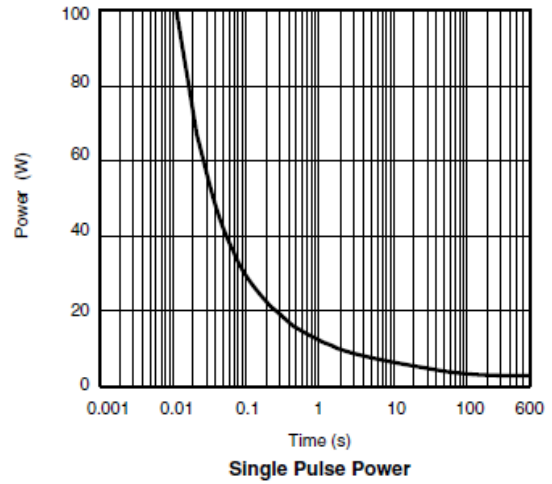
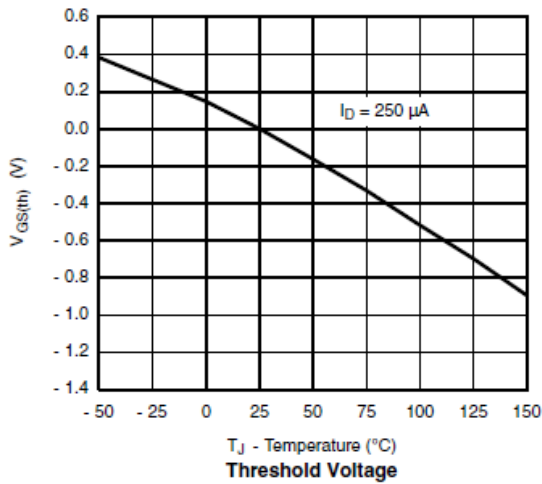
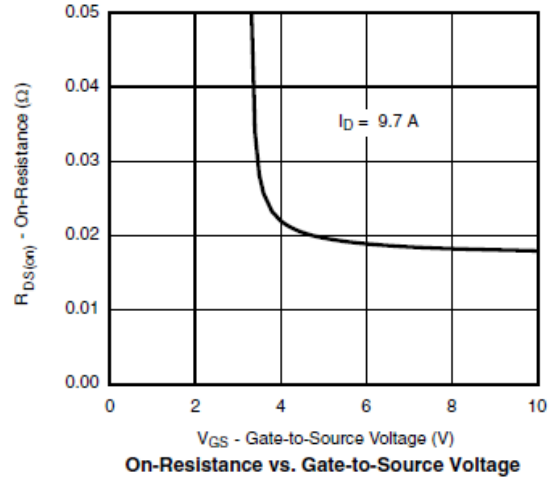
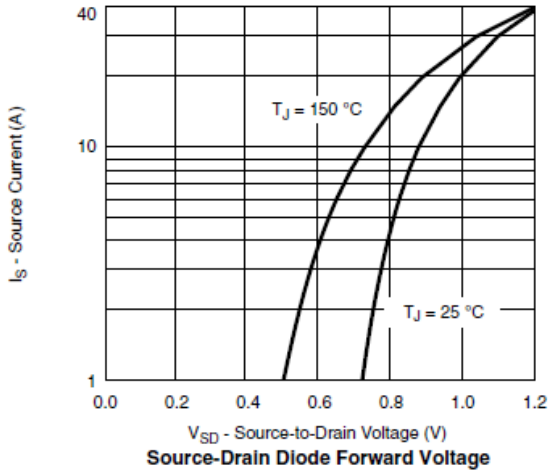


Typical Characteristics





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Typical Characteristics

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

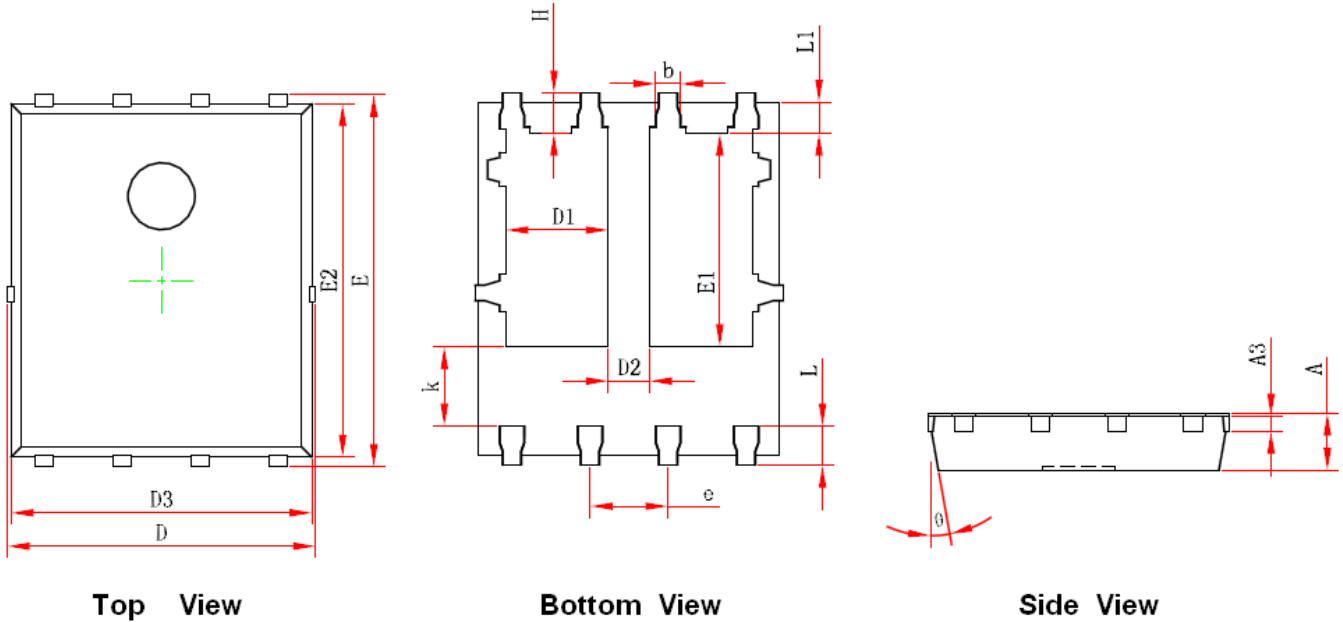


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (DFN 5X6-8L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254 REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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